

JAPANESE PATENT OFFICE  
PATENT JOURNAL  
KOKAI PATENT APPLICATION NO. SHO 62[1987]-90957

Int. Cl.<sup>4</sup>: H 01 L 25/04  
21/92

Sequence Nos. for Office Use: 7638-5F  
6708-5F

Application No.: Sho 60[1985]-231555

Application Date: October 17, 1985

Publication Date: April 25, 1987

No. of Inventions: 2 (Total of 4 pages)

Examination Request: Not requested

SEMICONDUCTOR DEVICE MANUFACTURING METHOD

Inventor: Kenzo Hata,  
Matsushita Denki Sangyo  
K.K.,  
1006 Oaza-kadoma,  
Kadoma-shi

Applicant: Matsushita Denki Sangyo  
K.K.,  
1006 Oaza-kadoma,  
Kadoma-shi

Agents: Toshio Nakao, patent  
attorney, and 1 other

[There are no amendments to this patent.]

Claims

1. A semiconductor device manufacturing method consisting of a process wherein a metal projection corresponding to the electrode on a second substrate, formed on a transfer substrate, is transferred and bonded onto an electrode on the aforementioned second substrate having at least an electrode formed in a position corresponding to the electrode on a first substrate on which a semiconductor element is formed, as well as an external connection electrode, and on which a semiconductor element is formed, as well as consisting of a process wherein an external connecting lead is bonded to a metal projection on the aforementioned external connecting electrode on the second substrate, and a process wherein next the electrode on the aforementioned first substrate and an electrode corresponding to the electrode on the aforementioned first substrate on the aforementioned second substrate are positioned together, with the aforementioned first or second substrate being subjected to pressure and heated, and with the electrodes on the aforementioned first and second substrates being bonded to each other via the metal projection.

2. A semiconductor device manufacturing method consisting of a process wherein a metal projection formed on a transfer substrate is transferred and bonded, an electrode--corresponding to the electrode on a second substrate on which a semiconductor element is formed, on a first substrate, on which a semiconductor element is formed, and an electrode on the aforementioned second substrate being positioned together, with the aforementioned first or second substrate being subjected to pressure and heated, and with the electrodes on the aforementioned first and second

substrates being bonded to each other via the metal projection, as well as consisting of a process wherein the metal projection on the external connecting electrode on the aforementioned first substrate and an external connecting lead are bonded.

\* \* \*